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74HC240; 74HCT240

Octal buffer/line driver; 3-state; inverting

Rev. 03 — 2 August 2007

Product data sheet

1. General description

The 74HC240; 74HCT240 is a high-speed Si-gate CMOS device and is pin compatible with Low-Power Schottky TTL (LSTTL).

The 74HC240; 74HCT240 is a dual octal inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs $\overline{1OE}$ and $\overline{2OE}$. A HIGH on $\overline{nOE}$ causes the outputs to assume a high impedance OFF-state.

The 74HC240; 74HCT240 is similar to the 74HC244; 74HCT244 but has inverting outputs.

2. Features

- Inverting 3-state outputs
- Multiple package options
- Complies with JEDEC standard no. 7 A
- ESD protection:
 - ◆ HBM JESD22-A114-D exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

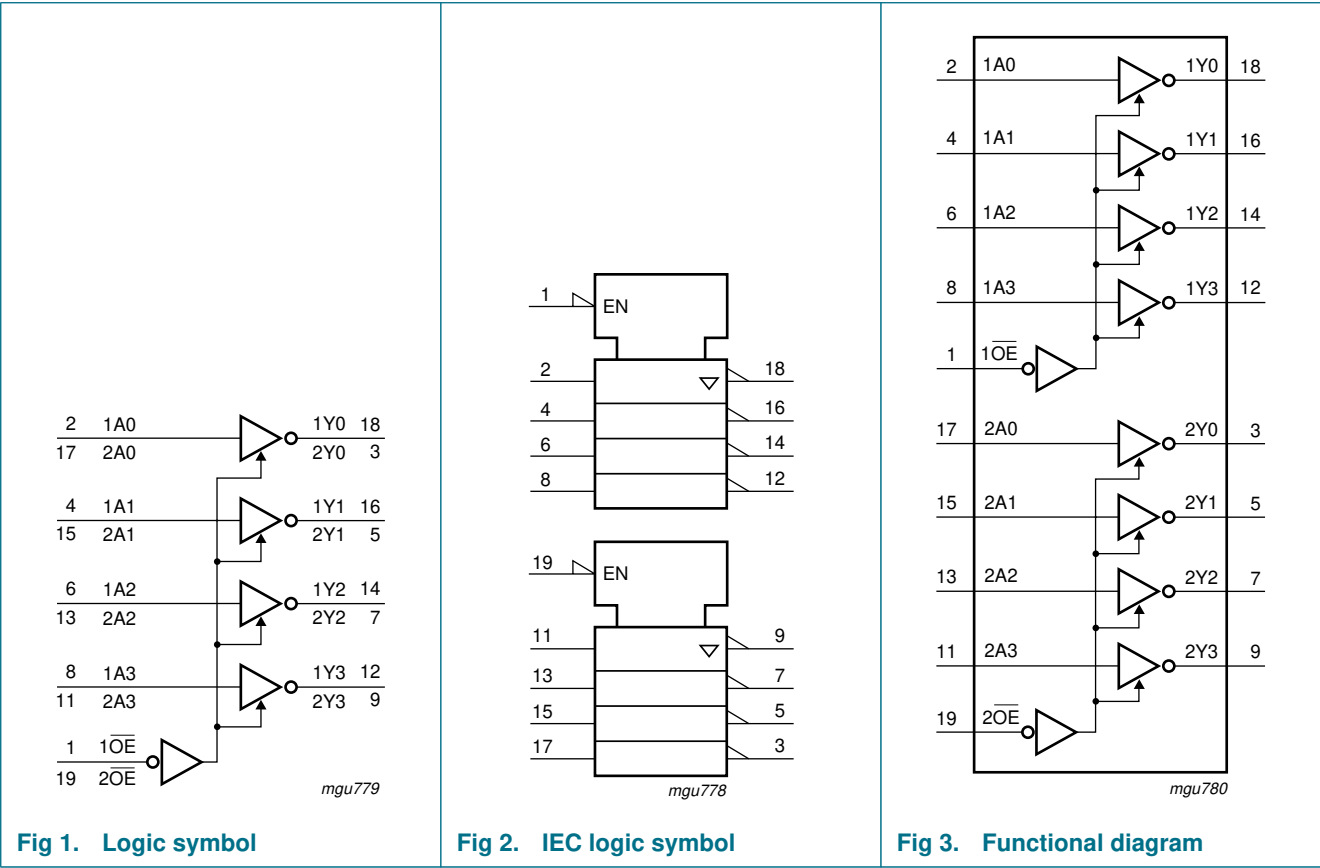
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC240				
74HC240N	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1
74HC240D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74HC240DB	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74HC240PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74HC240BQ	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85\text{ mm}$	SOT764-1
74HCT240				
74HCT240N	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1

Table 1. Ordering information ...continued

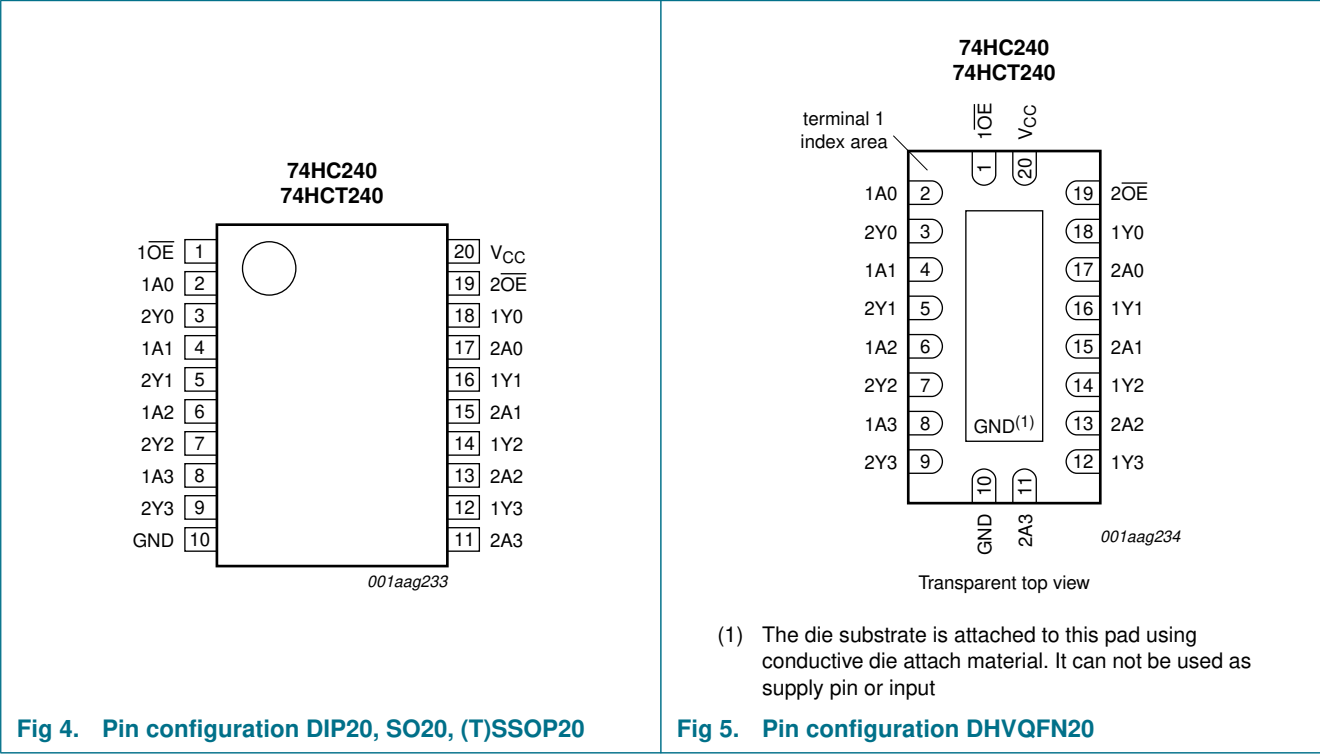
Type number	Package			
	Temperature range	Name	Description	Version
74HCT240D	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74HCT240DB	−40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74HCT240PW	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74HCT240BQ	−40 °C to +125 °C	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1OE	1	output enable input (active LOW)
1A0	2	data input
2Y0	3	bus output
1A1	4	data input
2Y1	5	bus output
1A2	6	data input
2Y2	7	bus output
1A3	8	data input
2Y3	9	bus output
GND	10	ground (0 V)
2A3	11	data input
1Y3	12	bus output
2A2	13	data input
1Y2	14	bus output
2A1	15	data input
1Y1	16	bus output

Table 2. Pin description ...continued

Symbol	Pin	Description
2A0	17	data input
1Y0	18	bus output
$\overline{2OE}$	19	output enable input (active LOW)
V _{CC}	20	supply voltage

6. Functional description

Table 3. Function table^[1]

Input		Output
n $\overline{OE}$	nAn	nYn
L	L	H
L	H	L
H	X	Z

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	-	±20	mA
I _O	output current	-0.5 V < V _O < V _{CC} + 0.5 V	-	±35	mA
I _{CC}	supply current		-	70	mA
I _{GND}	ground current		-70	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		^[1]		
	DIP20 package		-	750	mW
	SO20, SSOP20, TSSOP20 and DHVQFN20 packages		-	500	mW

- [1] For DIP20 packages: above 70 °C, P_{tot} derates linearly with 12 mW/K.
 For SO20 packages: above 70 °C, P_{tot} derates linearly with 8 mW/K.
 For SSOP20 and TSSOP20 packages: above 60 °C, P_{tot} derates linearly with 5.5 mW/K.
 For DHVQFN20 packages: above 60 °C, P_{tot} derates linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74HC240						
V_{CC}	supply voltage		2.0	5.0	6.0	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	ns/V
T_{amb}	ambient temperature		-40	-	+125	°C
74HCT240						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 4.5\text{ V}$	-	1.67	139	ns/V
T_{amb}	ambient temperature		-40	-	+125	°C

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC240										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = −6.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I _O = −7.8 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I _{OZ}	OFF-state output current	per input pin; V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; other inputs at V _{CC} or GND; V _{CC} = 6.0 V; I _O = 0 A	-	-	±0.5	-	±5.0	-	±10	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	µA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT240										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -20 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 6.0 mA	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I _{OZ}	OFF-state output current	per input pin; V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; other inputs at V _{CC} or GND; V _{CC} = 5.5 V; I _O = 0 A	-	-	±0.5	-	±5.0	-	±10	µA
I _{CC}	supply current	V _I = V _{CC} or GND; V _{CC} = 5.5 V; I _O = 0 A	-	-	8.0	-	80	-	160	µA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} - 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A								
		nAn or inputs	-	150	540	-	675	-	735	µA
		nOE input	-	70	252	-	315	-	343	µA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics
GND = 0 V; for load circuit see Figure 8.

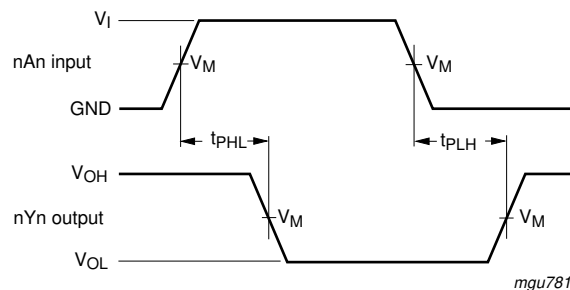
Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C		Unit	
			Min	Typ	Max	Max (85 °C)	Max (125 °C)		
74HC240									
t _{pd}	propagation delay	nAn to nYn; see Figure 6	[1]						
		V _{CC} = 2.0 V	-	30	100	125	150	ns	
		V _{CC} = 4.5 V	-	11	20	25	30	ns	
		V _{CC} = 5.0 V; C _L = 15 pF	-	9	-	-	-	ns	
		V _{CC} = 6.0 V	-	9	17	21	26	ns	
t _{en}	enable time	nOE to nYn; see Figure 7	[2]						
		V _{CC} = 2.0 V	-	39	150	190	225	ns	
		V _{CC} = 4.5 V	-	14	30	38	45	ns	
		V _{CC} = 6.0 V	-	11	26	33	38	ns	
t _{dis}	disable time	nOE to nYn or see Figure 7	[3]						
		V _{CC} = 2.0 V	-	41	150	190	225	ns	
		V _{CC} = 4.5 V	-	15	30	38	45	ns	
		V _{CC} = 6.0 V	-	12	26	33	38	ns	
t _t	transition time	see Figure 6	[4]						
		V _{CC} = 2.0 V	-	14	60	75	90	ns	
		V _{CC} = 4.5 V	-	5	12	15	18	ns	
		V _{CC} = 6.0 V	-	4	10	13	15	ns	
C _{PD}	power dissipation capacitance	per transceiver; V _I = GND to V _{CC}	[5]	-	30	-	-	-	pF

Table 7. Dynamic characteristics ...continued
GND = 0 V; for load circuit see Figure 8.

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C		Unit	
			Min	Typ	Max	Max (85 °C)	Max (125 °C)		
74HCT240									
t _{pd}	propagation delay	nAn to nYn; see Figure 6	[1]						
		V _{CC} = 4.5 V	-	11	20	25	30	ns	
		V _{CC} = 5.0 V; C _L = 15 pF	-	9	-	-	-	ns	
t _{en}	enable time	nOE to nYn; V _{CC} = 4.5 V; see Figure 7	[2]	-	13	30	38	45	ns
t _{dis}	disable time	nOE to nYn; V _{CC} = 4.5 V; see Figure 7	[3]	-	13	25	31	38	ns
t _t	transition time	V _{CC} = 4.5 V; see Figure 6	[4]	-	5	12	15	18	ns
C _{PD}	power dissipation capacitance	per transceiver; V _I = GND to V _{CC} – 1.5 V	[5]	-	30	-	-	-	pF

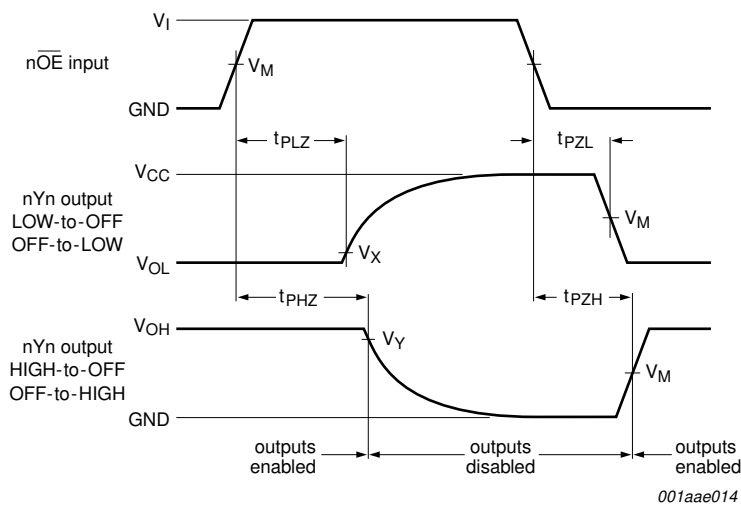
- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
 [2] t_{en} is the same as t_{PZH} and t_{PZL} .
 [3] t_{dis} is the same as t_{PHZ} and t_{PLZ} .
 [4] t_t is the same as t_{THL} and t_{TLH} .
 [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



Measurement points are given in Table 8.
 V_{OL} and V_{OH} are typical voltage output drop that occur with the output load.

Fig 6. Input (nAn) to output (nYn) propagation delays and output transition times

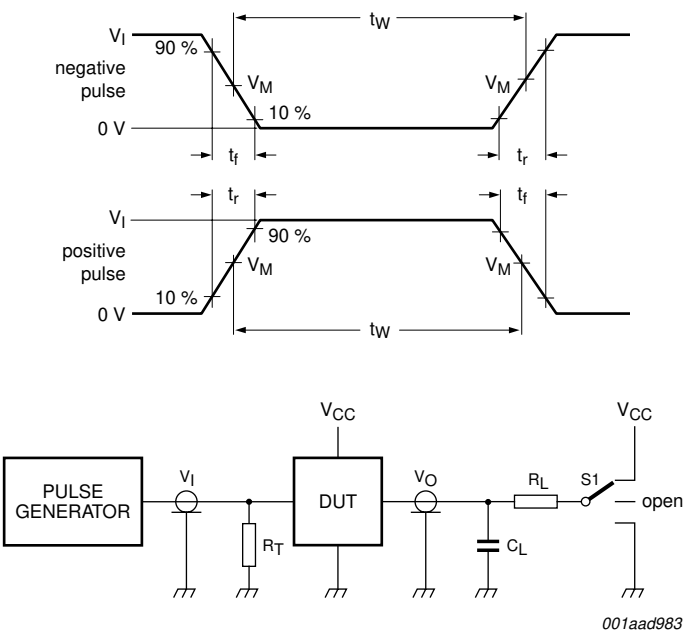


Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are typical voltage output drop that occur with the output load.

Fig 7. 3-state enable and disable times

Table 8. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC240	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$
74HCT240	1.3 V	1.3 V	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$



Test data is given in [Table 9](#).
Definitions test circuit:
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.
 C_L = Load capacitance including jig and probe capacitance.
 R_L = Load resistance.
 $S1$ = Test selection switch.

Fig 8. Load circuitry for measuring switching times

Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC240	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT240	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1

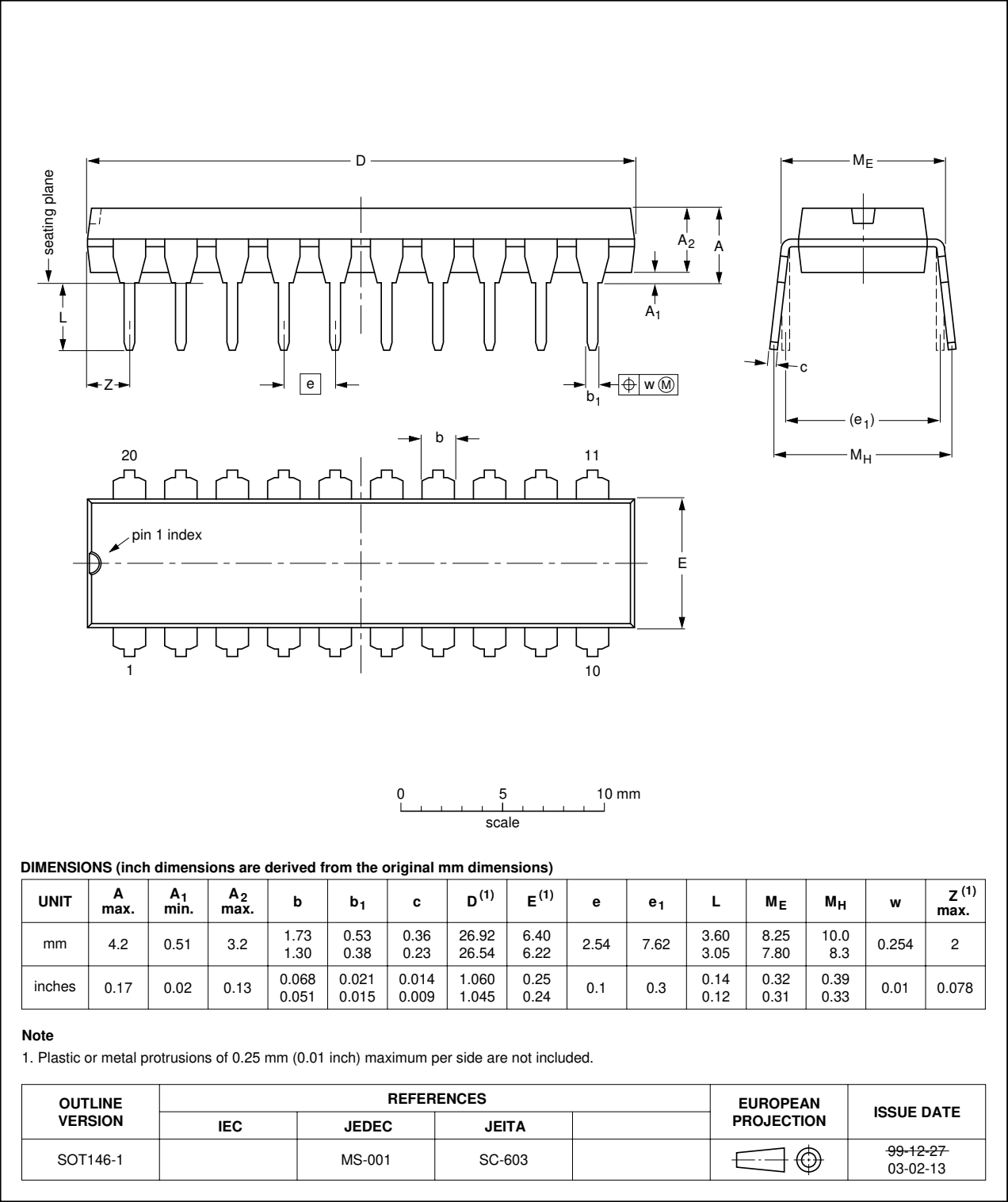


Fig 9. Package outline SOT146-1 (DIP20)

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

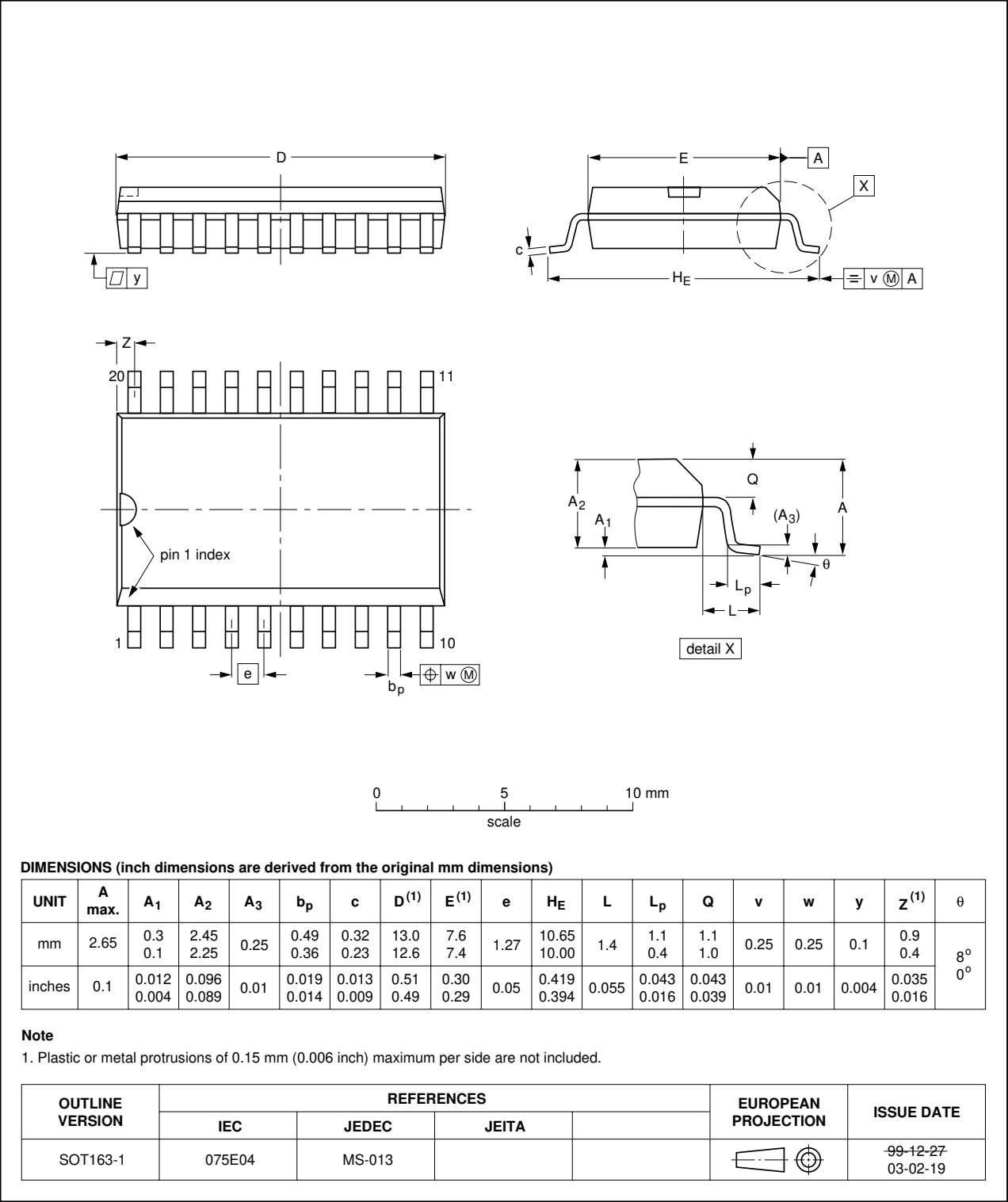
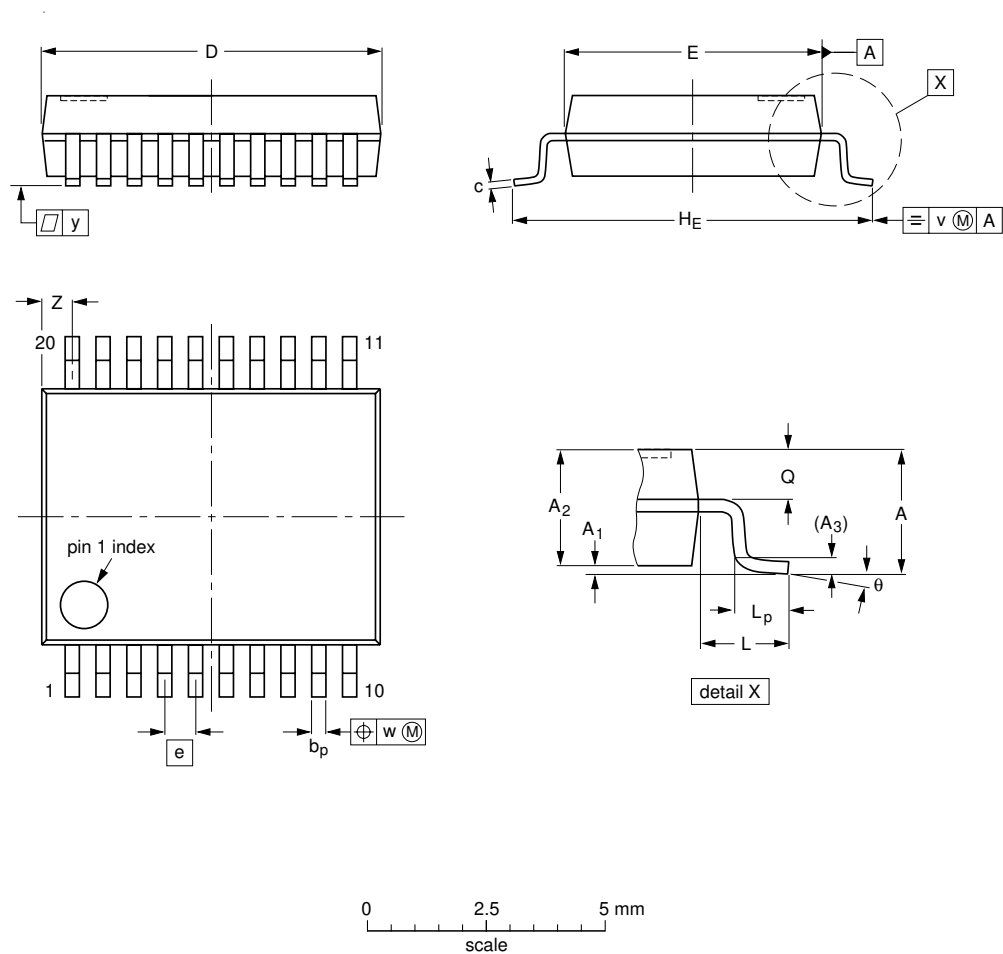


Fig 10. Package outline SOT163-1 (SO20)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1



DIMENSIONS (mm are the original dimensions)

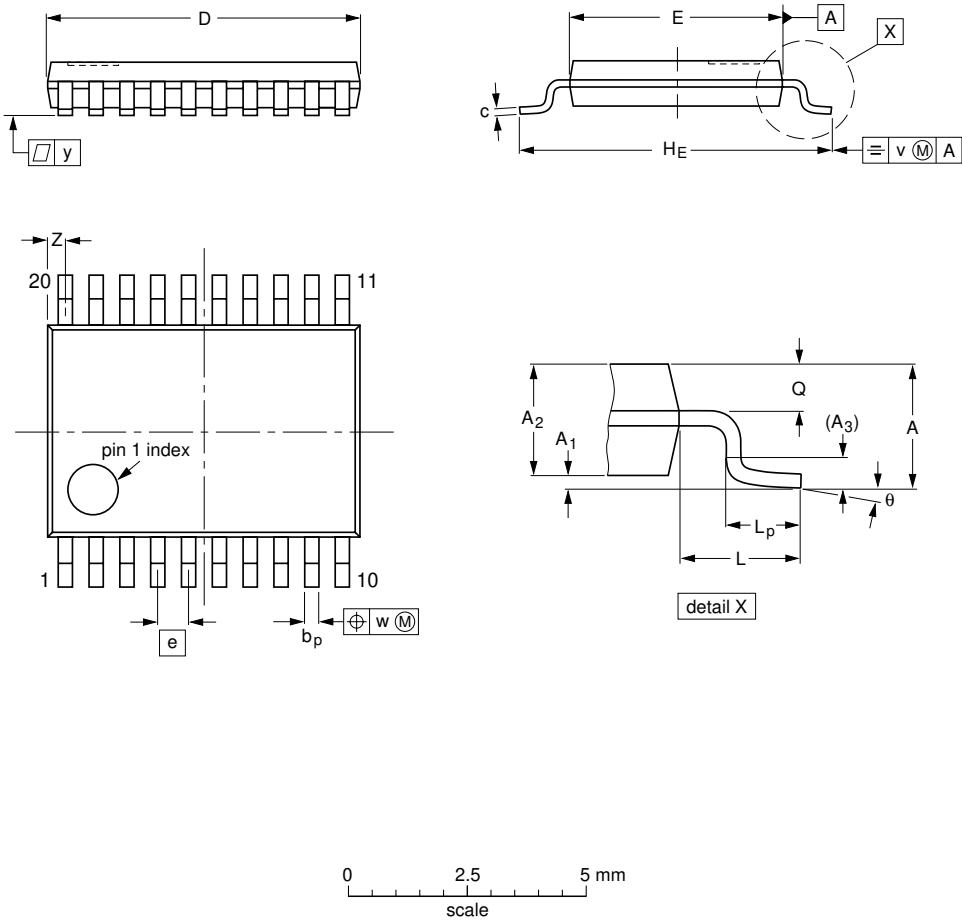
UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8° 0°

Note
 1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT339-1		MO-150				99-12-27 03-02-19

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

- Notes
- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
 - 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

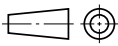
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT360-1		MO-153				-99-12-27 03-02-19

Fig 12. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm SOT764-1

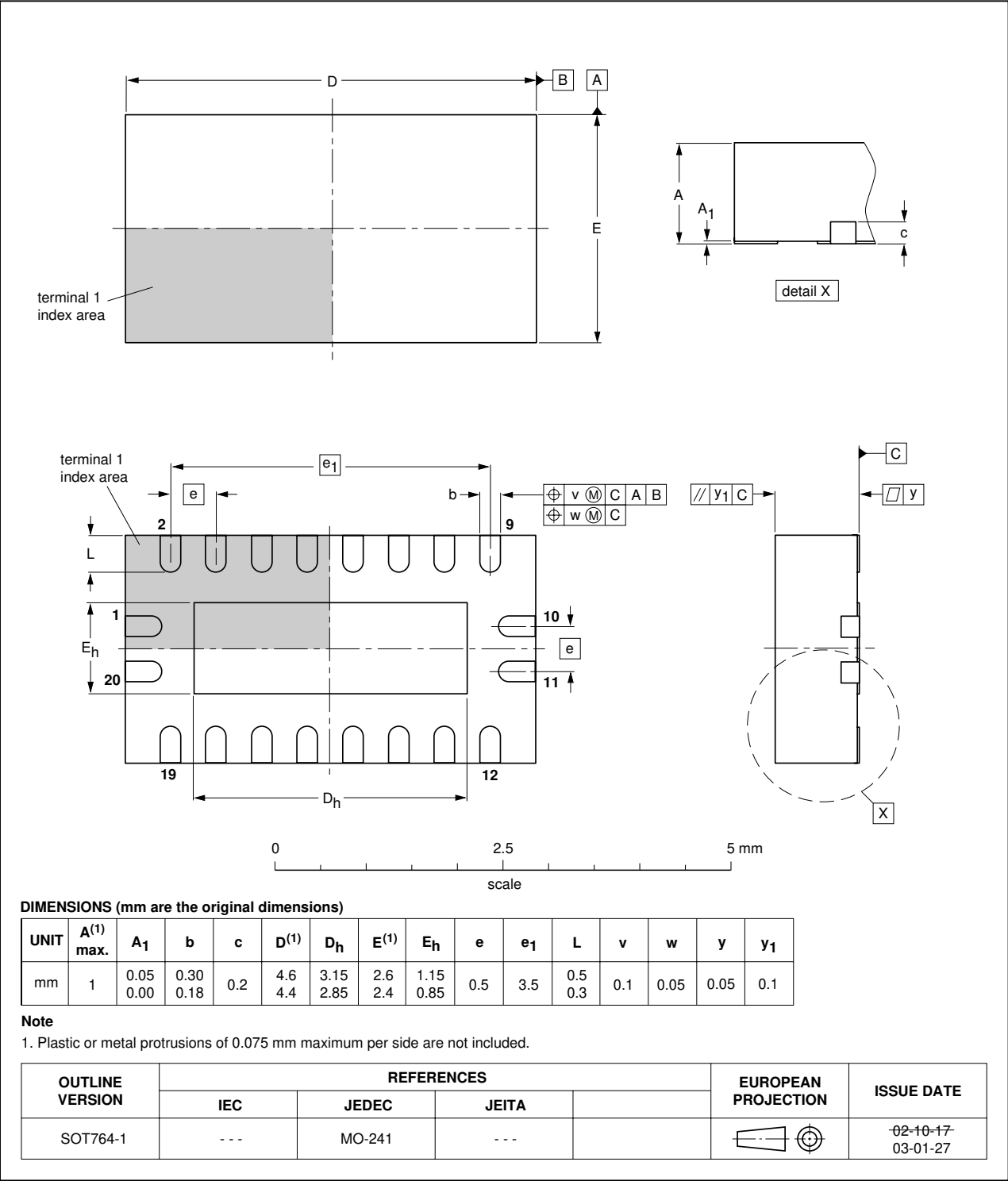


Fig 13. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT240_3	20070802	Product data sheet	-	74HC_HCT240_CNV_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Added type number 74HC240BQ and 74HCT240BQ (DHVQFN20 package)			
74HC_HCT240_CNV_2	19970828	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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